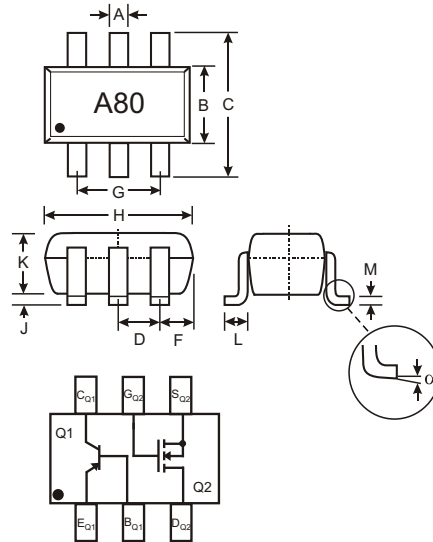


Features

- Combines MMBT4403 type transistor with 2N7002 type MOSFET
- Small Surface Mount Package
- NPN/P-Channel Complement Available: CTA2N1P
- Lead Free/RoHS Compliant (Note 1)

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking: A80, See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approx.)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J		0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
	0	8°
All Dimensions in mm		

Maximum Ratings, Total Device @ T_A = 25 C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 2)	P _d	150	mW
Thermal Resistance, Junction to Ambient (Note 2)	R _{JA}	833	C/W
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	C

Maximum Ratings, Q1, MMBT4403 PNP Transistor Element @ T_A = 25 C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-40	V
Collector-Emitter Voltage	V _{CE0}	-40	V
Emitter-Base Voltage	V _{EB0}	-5.0	V
Collector Current - Continuous	I _C	-600	mA

Maximum Ratings, Q2, 2N7002 N-Channel MOSFET Element @ T_A = 25 C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	60	V
Drain-Gate Voltage R _{GS} 1.0M	V _{DGR}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
		±40	
Drain Current (Note 2)	I _D	115	mA
		73	
		800	

Notes: 1. No purposefully added lead.

Electrical Characteristics, Q1, MMBT4403 PNP Transistor Element

@ T_A = 25 C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-40		V	I _C = -100 A, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-40		V	I _C = -1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0		V	I _E = -100 A, I _C = 0
Collector Cutoff Current	I _{CEX}		-100	nA	V _{CE} = -35V, V _{EB(OFF)} = -0.4V
Base Cutoff Current	I _{BL}		-100	nA	V _{CE} = -35V, V _{EB(OFF)} = -0.4V
ON CHARACTERISTICS (Note 3)					
DC Current Gain	h _{FE}	30 60 100 100 20	300		I _C = -100μA, V _{CE} = -1.0V I _C = -1.0mA, V _{CE} = -1.0V I _C = -10mA, V _{CE} = -1.0V I _C = -150mA, V _{CE} = -2.0V I _C = -500mA, V _{CE} = -2.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		-0.40 -0.75	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	-0.75	-0.95 -1.30	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{cb}		8.5	pF	V _{CB} = -10V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{eb}		30	pF	V _{EB} = -0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{ie}	1.5	15	k	V _{CE} = -10V, I _C = -1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h _{re}	0.1	8.0	x 10 ⁻⁴	
Small Signal Current Gain	h _{fe}	60	500		
Output Admittance	h _{oe}	1.0	100	S	
Current Gain-Bandwidth Product	f _T	200		MHz	V _{CE} = -10V, I _C = -20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d		15	ns	V _{CC} = -30V, I _C = -150mA, V _{BE(off)} = -2.0V, I _{B1} = -15mA
Rise Time	t _r		20	ns	
Storage Time	t _s		225	ns	V _{CC} = -30V, I _C = -150mA, I _{B1} = I _{B2} = -15mA
Fall Time	t _f		30	ns	

Electrical Characteristics, Q2, 2N7002 N-Channel MOSFET Element

@ T_A = 25 C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	70		V	V _{GS} = 0V, I _D = 10 A
Zero Gate Voltage Drain Current	I _{DSS}			1.0 500	μA	V _{DS} = 60V, V _{GS} = 0V @ T _C = 25°C @ T _C = 125°C
Gate-Body Leakage	I _{GSS}			±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	1.0		2.0	V	V _{DS} = V _{GS} , I _D = -250 A
Static Drain-Source On-Resistance	R _{DS(ON)}		3.2 4.4	7.5 13.5		V _{GS} = 5.0V, I _D = 0.05A V _{GS} = 10V, I _D = 0.5A @ T _J = 25°C @ T _J = 125°C
On-State Drain Current	I _{D(ON)}	0.5	1.0		A	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance	g _{FS}	80			mS	V _{DS} = 10V, I _D = 0.2A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}		22	50	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}		11	25	pF	
Reverse Transfer Capacitance	C _{rss}		2.0	5.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}		7.0	20	ns	V _{DD} = 30V, I _D = 0.2A, R _L = 150 Ω, V _{GEN} = 10V, R _{GEN} = 25 Ω
Turn-Off Delay Time	t _{D(OFF)}		11	20	ns	

Note: 2. Device mounted on FR-4 PCB; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

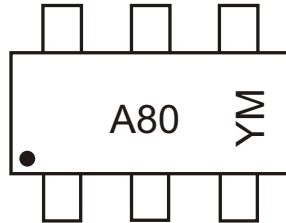
3. Short test pulse used to minimize self-heating effect.

Ordering Information (Note 4)

Device	Packaging	Shipping
CTA2P1N-7-F	SOT-363	3000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



A80 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: N = 2002
 M = Month ex: 9 = September

Date Code Key

Year	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

MMBT4403 Section

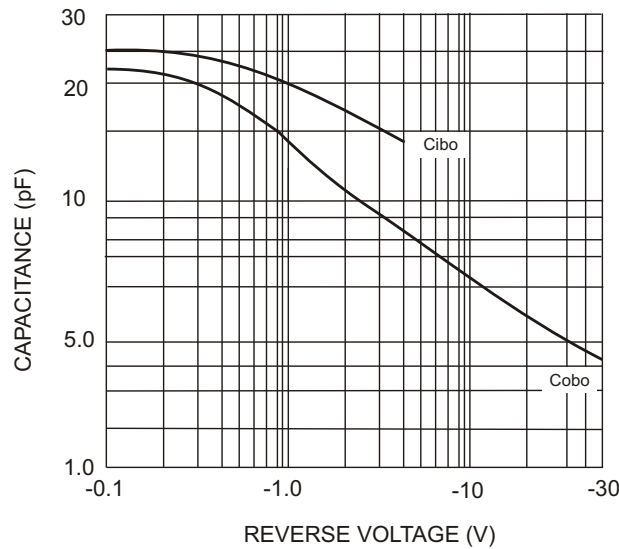


Fig. 1 Typical Capacitance

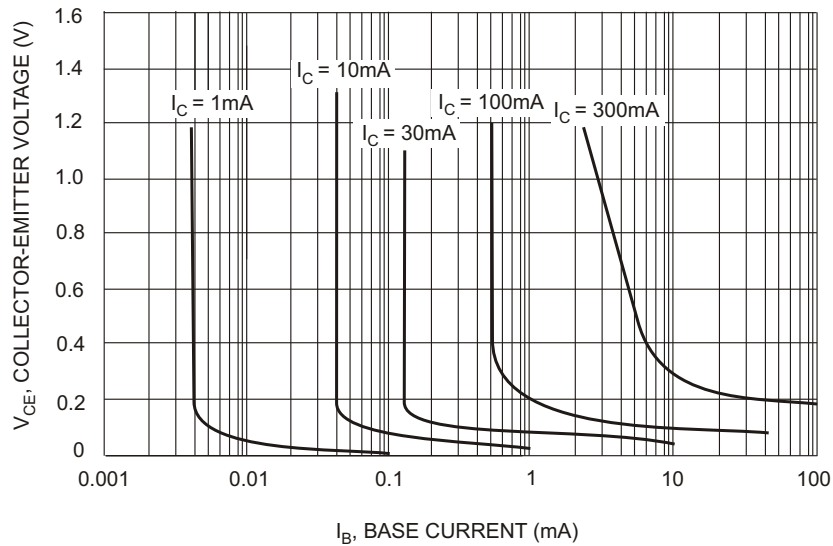


Fig. 2 Typical Collector Saturation Region

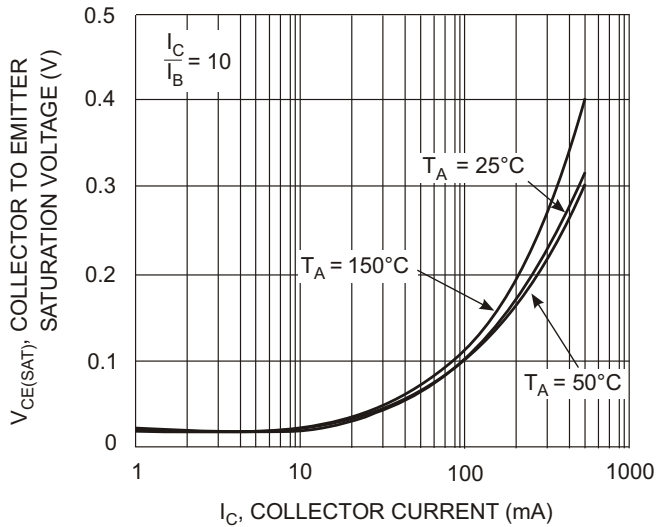


Fig. 3 Collector Emitter Saturation Voltage vs. Collector Current

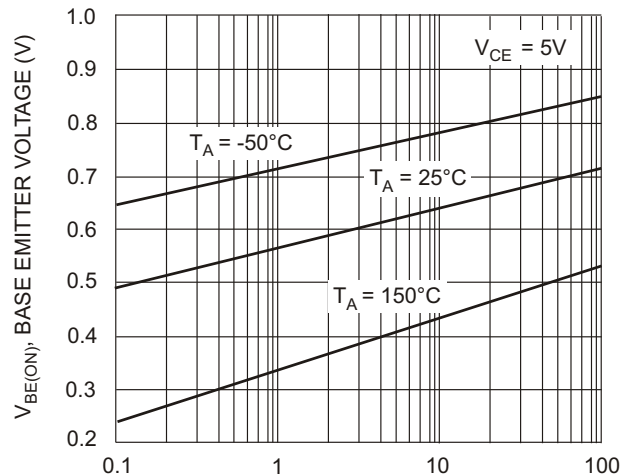


Fig. 4 Base-Emitter Voltage vs. Collector Current

MMBT4403 Section

NEW PRODUCT

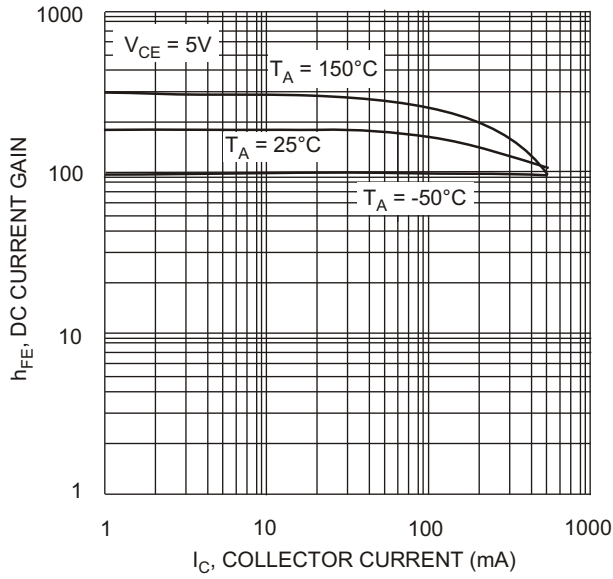


Fig. 5 DC Current Gain vs. Collector Current

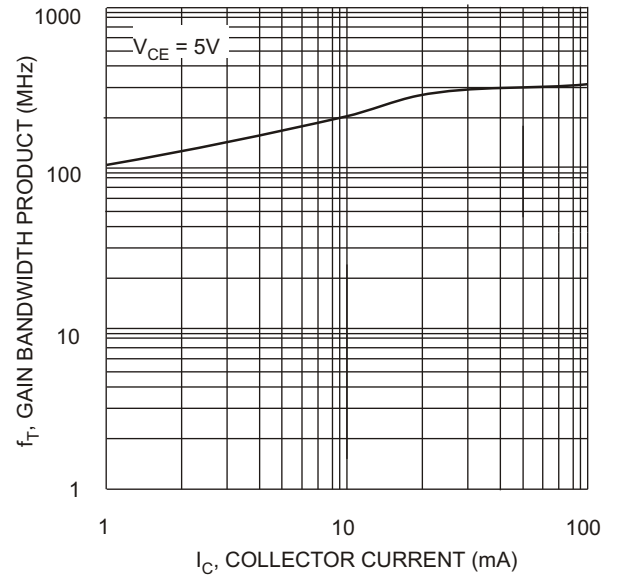


Fig. 6 Gain Bandwidth Product vs. Collector Current

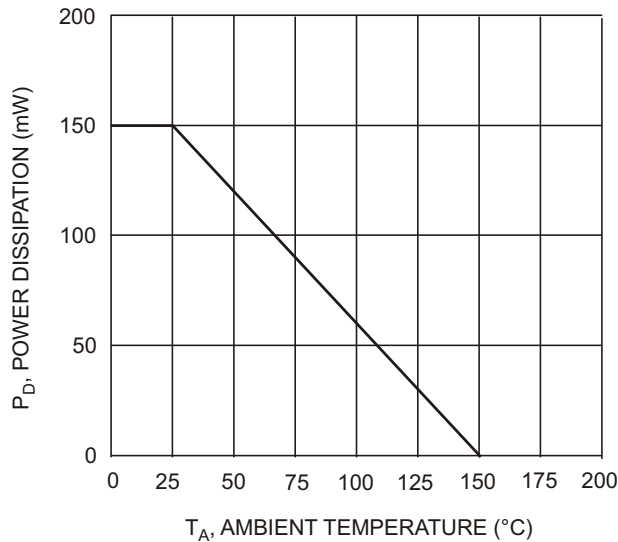


Fig. 7 Max Power Dissipation vs Ambient Temperature (Total Device)

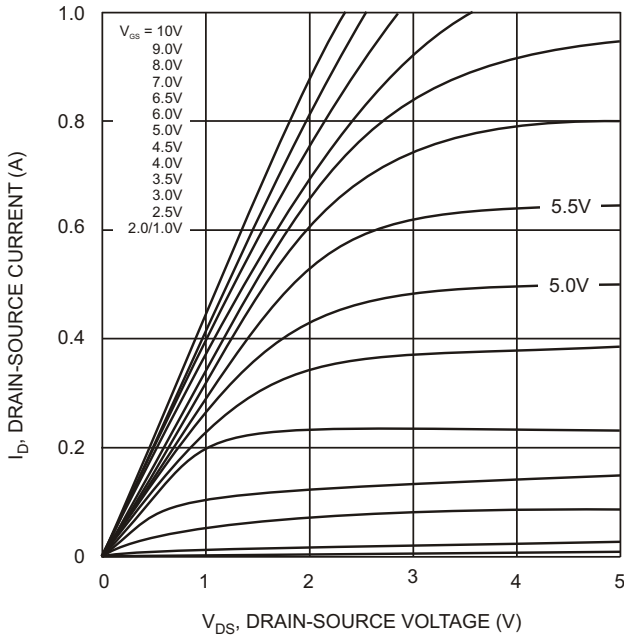


Fig. 8 On-Region Characteristics (2N7002)

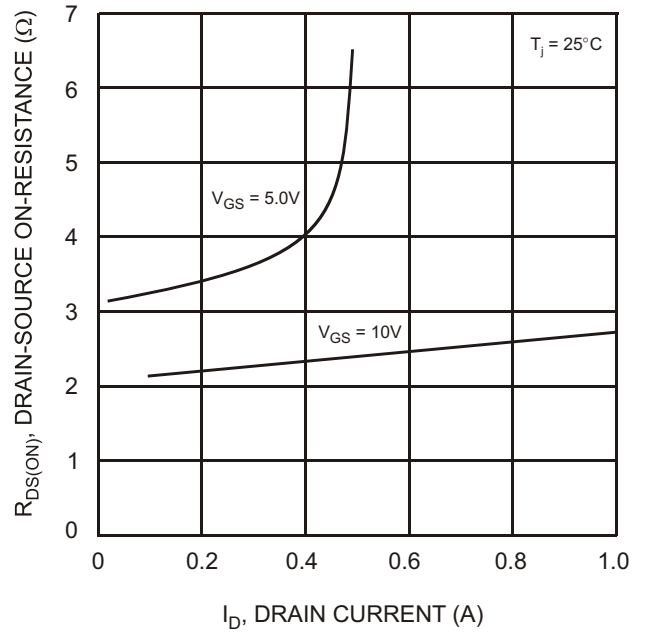


Fig. 9 On-Resistance vs Drain Current (2N7002)

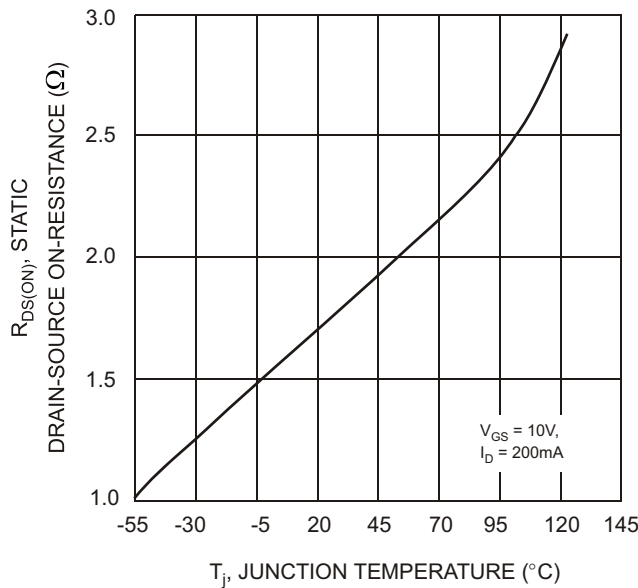


Fig. 10 On-Resistance vs Junction Temperature (2N7002)

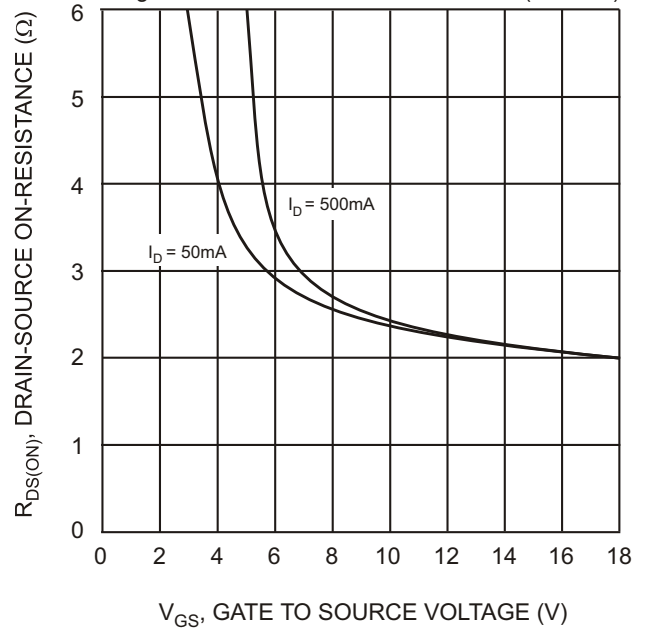


Fig. 11 On-Resistance vs. Gate-Source Voltage (2N7002)

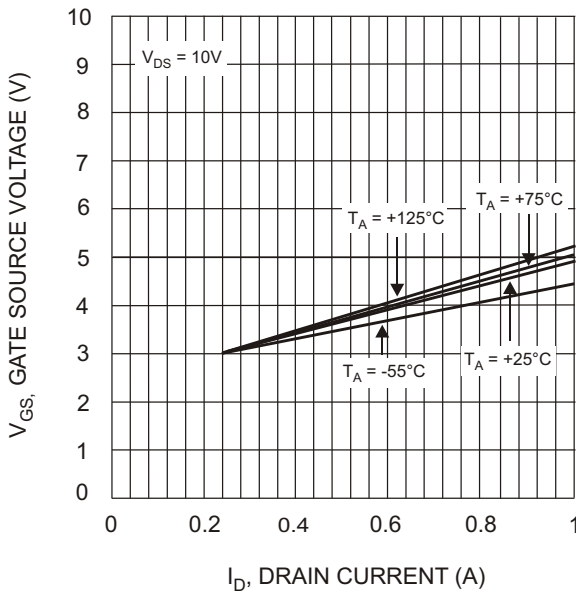


Fig. 12 Typical Transfer Characteristics (2N7002)

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